Supporting Information to

Facile 3D integration of Si nanowires on Bosch-etched sidewalls for stacked channel transistors

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Section 1 Structural characterizations of single silicon nanowire

Fig. S1 (a) and (b) show, respectively, the scanning electron microscopy (SEM) image and the transmission electron microscopy (TEM) images of a selected single SiNW with a diameter of ~66 nm.